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(71) Applicant: **SHARP CORP**

(72) Inventor:  
**KURAHASHI TAKANAO**  
**NAKATSU HIROSHI**  
**MURAKAMI TETSURO**  
**HOSOBANE HIROYUKI**

(54) **SEMICONDUCTOR LIGHT EMITTING ELEMENT**

(57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor light emitting element capable of emitting light with high efficiency by increasing the distance from an interface having lower crystallinity to an active layer by switching V group elements of As and P and suppressing decrease in the crystallinity of the active layer in an AlGaInP resonant cavity LED or a surface emitting laser.

**SOLUTION:** High reflectivity is assured by multilayer reflecting films 23 and 24 of a material different from a light emitting layer 26, a multilayer reflecting film of the same material as that of the light emitting layer is formed thereon, then the light emitting layer is formed, and the distance from an interface for switching the material to the active layer is increased.

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